



Applicants:

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Assignee:

Advanced Micro Devices, Inc.

Title:

Polished Flash Process With Metal Gates And Improved Planarity

Serial No.:

09/430,366

Filing Date:

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Chen, Jack

Group Art Unit:

2813

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M-7523 US

San Jose, California May 29, 2002

BOX RCE

COMMISSIONER FOR PATENTS

Washington, D. C. 20231

RESPONSE TO OFFICE ACTION (FINAL)

RECEIVED

Dear Sir:

This is a response to the Final Office Action dated February 12, 2002, which has a statutorily shortened period that ends on May 12, 2002. A one-month extension of time accompanies this Response, allowing the Applicants until June 12, 2002 to respond. Please enter the following amendments before taking action on the merits of the above-referenced application.

IN THE CLAIMS

The following is a clean version of the entire set of pending Claims 1, 3-7, 9-12, 14, 15 and 21-23. Claims 16-20 were withdrawn from consideration. In accordance with 37 CFR § 1.121(c)(1)(ii), an attachment provides marked up versions of the amended claims containing the newly introduced changes. Claims 7 and 21-23 are presently amended.

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(Thrice amended)

A method of making a flash memory cell including a

substrate and a floating gate, the method comprising:

862678 v1

-1-

Serial No. 09/430,366